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PATENT ABSTRACTS OF JAPAN(21) Application number: **63067394**(51) Intl. Cl.: **H01J 37/09 H01J 37/244**(22) Application date: **23.03.88**

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states:(71) Applicant: **HITACHI LTD**(72) Inventor: **SAITO NORIO**

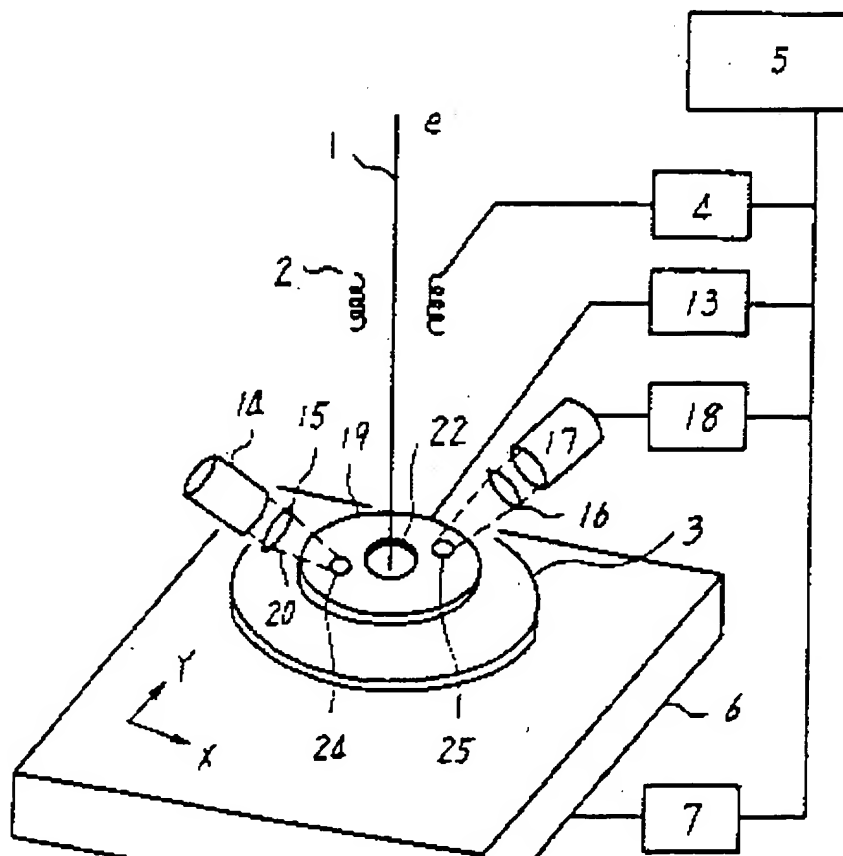
(74) Representative:

**(54) CHARGED BEAM
DETECTOR**

(57) Abstract:

PURPOSE: To improve the image drawing accuracy by providing a hole to pass charged beams on the detection surface and arranging holes or cuttings to pass the other beams at both sides of the hole.

CONSTITUTION: The electron detector 19 is a ring form, and not only a passage 27 of electron beams 1, but also passages 24 and 25 to pass the light are arranged. As a result, the light 20 emitted from a light source 14 passes through the passages 24 and 25, enters a receiver 17, and the height of the beam axis 23 can be detected. In this case, the focus yield of electron is made larger several times compared with the case of using four small electron detectors. As a result, since the height of a wafer immediately under the beam axis can be measured, as well as the marking position detecting accuracy is increased, the



deflection sensitivity correction can
be made correctly and the image
drawing accuracy can be improved.

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JP1241745A2: CHARGED BEAM DETECTOR

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Inventor(s):

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Applicant/Assignee:

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Abstract:

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Constitution: The electron detector 19 is a ring form, and not only a passage 27 of electron beams 1, but also passages 24 and 25 to pass the light are arranged. As a result, the light 20 emitted from a light source 14 passes through the passages 24 and 25, enters a receiver 17, and the height of the beam axis 23 can be detected. In this case, the focus yield of electron is made larger several times compared with the case of using four small electron detectors. As a result, since the height of a wafer immediately under the beam axis can be measured, as well as the marking position detecting accuracy is increased, the deflection sensitivity correction can be made correctly and the image drawing accuracy can be improved.

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